Icemos Technology Ltd Product Specification 1003.291501 Issue Date 31 October 2016 09:1

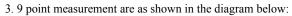
| Part Number | Customer |
|-------------|----------|
| Fait Number | Customer |

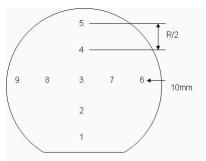
| Category | | Parameter | Specification | Measurement Method |
|---------------|------|---------------------------------|--|------------------------------|
| OverallWafer | 1.0 | Diameter | 150.00 +/- 0.50 mm | WaferVendor |
| | 2.0 | Primary Flat Length | 57.50 +/- 2.50 mm | Wafer Vendor |
| | 3.0 | Primary Flat Orientation | {110}+/-1 degree | Wafer Vendor |
| | 4.0 | Growth Method | CZ | Wafer Vendor |
| | 5.0 | Туре | Any | Wafer Vendor |
| | 6.0 | Dopant | Any | Wafer Vendor |
| | 7.0 | Resistivity | 0.1∼ 100 ohm cm | Wafer Vendor |
| | 8.0 | Overall Thickness | 777.00 +/- 5.00 um | Wafer Vendor |
| | 9.0 | Total Thickness Variation (TTV) | <3.00um | Guaranteed by process |
| | 10.0 | Bow | <50.00um | ADE to ASTM F534, 20% |
| | 11.0 | Warp | <50.00um | ADE to ASTM F657, 20% |
| | 12.0 | Lasermarking | On wafer FRONTSIDE opposite the flat. Scribe format: [ICE-6-777.XXXX] (unique scribe) | Guaranteed by process |
| | 13.0 | Orientation | <100> +/-0.5 | Wafer Vendor |
| | 14.0 | Back Surface Quality | Polished, with light handling marks. | Guaranteed by process |
| | 15.0 | Front Surface Quality | Prime polished. | Guaranteed by process |
| | 16.0 | Edge Chips | None | Bright Light 100% (note 2) |
| HandleSilicon | 17.0 | Handle Thickness | 777.00 +/- 5.00 um | ADE |
| | 18.0 | Surface Haze | None | Bright Light, 100% (note 2). |
| | 19.0 | Total scratch length | None | Bright Light, 100% (note 2). |

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| Part Number | | Customer | | |
|-------------------|--|---|--------------------|--|
| Category | Parameter | Specification | Measurement Method | |
| Shipping Details | Wafer per box: | Max 25 | | |
| | Packaging: | Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging | | |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness | | |
| Explanatory Notes | 1. Microscope inspec | tion performed using microscope scan as below. 5x objective. | | |
| | 2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall | | | |

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information

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